

GAE GREAT AMERICAN ELECTROINCS

2N5591/B25-12

Silicon NPN power VHF transistor 2N55591/B25-12 is designed for use 12.6 volt power amplifier, frequency multipliers and oscillator applications in industrial and commercial equipment. Especially suited for AM/FM land and mobile operation.

Output Power: 20 Watt
 Frequency Range: 50-200 Mhz
 Voltage: 12.6 V
 Package Type: MT-72
 Common Emitter Configuration
 NiChrome Resistors
 Aluminum Metalization

Electrical Characteristics ($T_{CASE}=40^{\circ}C$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{out}	$f_o = 175 \text{ Mhz}/V_{cc}=12.6V/P_{IN}=6.7W$	20			W
G_p	$f_o = 175 \text{ Mhz}/V_{cc}=12.6V/P_{out}=20W$	5			dB
λ_c	$f_o = 175 \text{ Mhz}/V_{cc}=12.6V/P_{out}=20W$	60	70	80	%

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

SYMBOL	PARAMETERS	VALUE	UNIT
V_{CER}	Collector-Emitter Voltage $R_{EB} \leq 100\Omega$	36	V
V_{EBO}	Emitter-Base Voltage	4	V
I_c	Continuous Collector Current	3	A
P_C	Collector Power Dissipation	25*	W
T_j	Junction Temperature	150	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	4	$^{\circ}C/W$

*For Dynamic Operation, $T_{CASE} = 50^{\circ}C$